

L Number	Hits	Search Text	DB	Time stamp
1	741	@ad<=20020322 and (257/310).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:30
2	551	@ad<=20020322 and (257/410).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:33
3	531	@ad<=20020322 and (257/411).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:33
4	957	@ad<=20020322 and (257/412).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:33
5	411	@ad<=20020322 and (257/413).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:33
6	153	@ad<=20020322 and (438/216).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:51
7	855	@ad<=20020322 and (438/240).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:51
8	24	@ad<=20020322 and 'MOS' same 'high dielectric' with 'gate' same 'nitride'	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 16:12
9	21	@ad<=20020322 and 'MOS' same 'gate' with 'high k' same 'nitride'	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 16:13
-	2	"20030178674"	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/30 12:50
-	1985	@ad<=20020322 and (257/410-413).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:32
-	143	@ad<=20020322 and (438/216).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/14 15:50
-	318	@ad<=20020322 and (438/261).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/30 10:57
-	713	@ad<=20020322 and (438/287).ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/30 10:58

-	844	@ad<=20020322 and (438/585).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:00
-	448	@ad<=20020322 and (438/587-588).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:00
-	317	@ad<=20020322 and (438/591).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:04
-	298	@ad<=20020322 and (438/791).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:04
-	196	@ad<=20020322 and (438/792).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:05
-	50	@ad<=20020322 and 'MOS' same 'high dielectric' with 'nitride'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:10
-	9	@ad<=20020322 and 'MOS' same 'Hafnium oxide' with 'nitride'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/29 14:38
-	196	@ad<=20020322 and 'MOS' same 'aluminum oxide' with 'nitride'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 12:06
-	16	@ad<=20020322 and 'high dielectric' same 'aluminum oxide' same 'nitride layer'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 11:33
-	3	@ad<=20020322 and 'MOS' same 'high dielectric constant' same 'nitridation'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/14 16:02
-	302	@ad<=20020322 and 'high dielectric constant' and 'nitridation'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/31 07:55
-	14	@ad<=20020322 and 'high dielectric constant' and 'plasma nitriding'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 12:09
-	2	"20020137317"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 12:23
-	2	("6482694").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/30 12:24

-	2	("6339246").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/30 12:24
-	24	bai-gang.in.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/30 12:51
-	50	@ad<=20020322 and 'nitridation' same 'high dielectric'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/29 14:05
-	5	@ad<=20020322 and 'plasmas' adj1 'nitridation' same 'high dielectric'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 07:56
-	3	@ad<=20020322 and 'plasmas' adj1 'nitriding' same 'high dielectric'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 07:56
-	5	@ad<=20020322 and 'plasma nitridation' same 'high dielectric'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:15
-	162	@ad<=20020322 and 'nitride layer' with 'high dielectric'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:33
-	128	@ad<=20020322 and 'nitride layer' with 'tantalum oxide'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:49
-	76	@ad<=20020322 and 'polysilicon' same 'tantalum oxide' same 'nitride layer'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:32
-	46	@ad<=20020322 and 'nitride layer' with 'high k'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 09:36
-	102	@ad<=20020322 and 'p-type polysilicon gate' same 'n-type polysilicon gate'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 10:33
-	140	@ad<=20020322 and 'p-type polysilicon' with 'boron'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 10:35
-	35	@ad<=20020322 and 'p-type polysilicon gate' with 'boron'	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 10:36
-	1	"6291868".PN.	USPAT	2003/12/31 10:42
-	2	("6436848").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/29 13:29

-	42	@ad<=20020322 and 'MOS' and 'HfO.sub.2' with 'ZrO.sub.2' with 'nitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07 15:39
-	128	@ad<=20020322 and 'MOS' and 'high k' with 'nitride'		2004/09/07 15:39